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in the following listed application(s) or patent(s) for which the issue fee has been paid.

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Respectfully Submitted,



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(12) **United States Patent**
Nakamura

(10) **Patent No.:** **US 7,554,117 B2**
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(54) **SEMICONDUCTOR DEVICE AND
MANUFACTURING METHOD THEREOF**

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See application file for complete search history.

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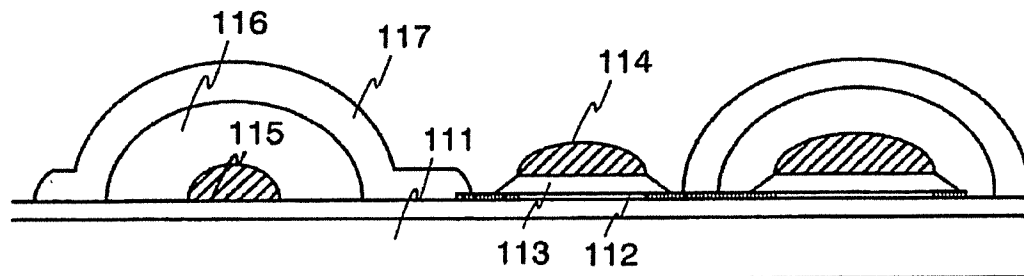
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(57) **ABSTRACT**

An island-like interlayer insulating film is formed selectively
in a region where a source interconnection and a gate inter-
connection intersect. For example, by use of ink jet method, a
solution containing an insulating material is dropped on a
region where the gate interconnection and the source inter-
connection intersect or a region where a holding capacitor is
formed, that enable to reduce a photolithography process and
to reduce the number of masks that are used in a TFT.

18 Claims, 7 Drawing Sheets



(intersection of interconnections)

(TFT)

(holding capacitor)